

Abstract of the Disclosure

A semiconductor device adopting shallow trench isolation for reducing an internal stress of a semiconductor substrate. The semiconductor device is composed of a semiconductor substrate provided with a trench for isolation, and an insulating film formed to cover the trench for relaxing an internal stress of the semiconductor substrate. The insulating film includes a first portion disposed to be opposed to a bottom of the trench, and a second portion disposed to be opposed to a side of the trench. A first thickness of the first portion is different from a second thickness of the second portion.